

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED TYPE

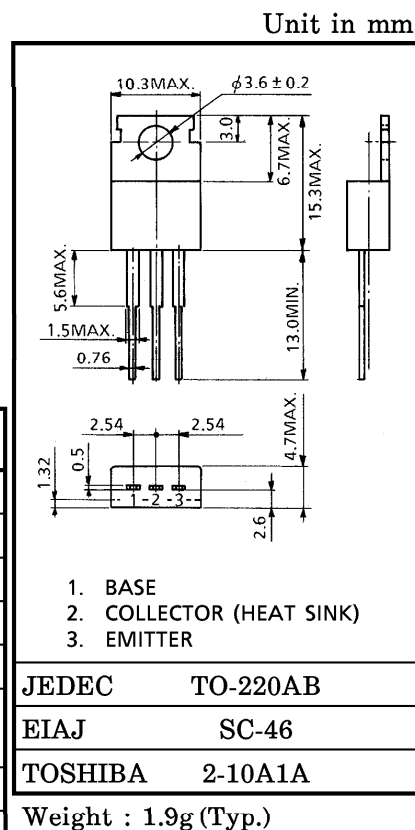
## 2SD525

## POWER AMPLIFIER APPLICATIONS

- High Breakdown Voltage :  $V_{CEO}=100V$
- Low Collector Saturation Voltage :  $V_{CE(sat)}=2.0V$  (Max.)
- Complementary to 2SB595.
- Recommend for 30W High Fidelity Audio Frequency Amplifier Output Stage.

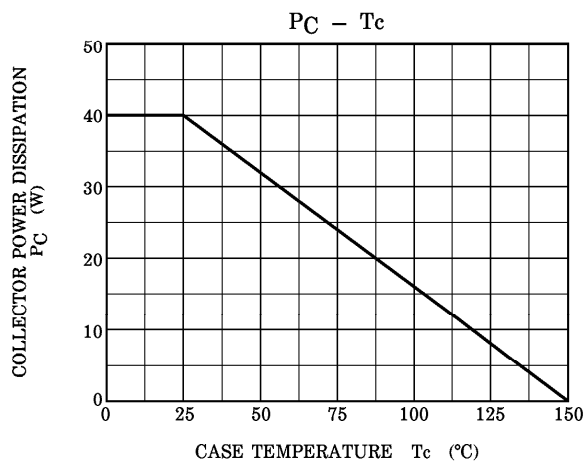
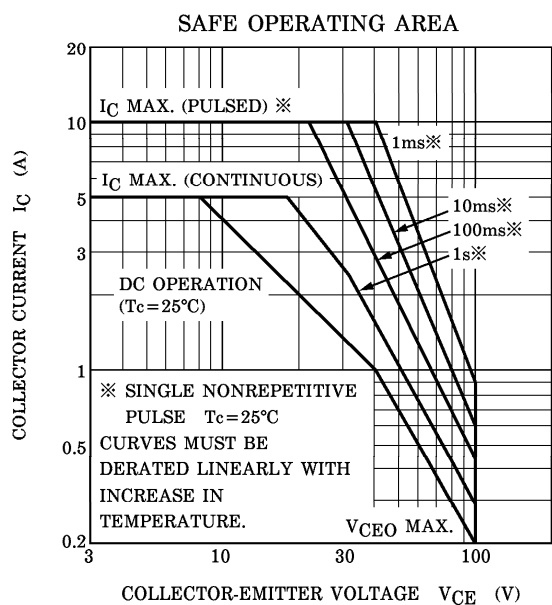
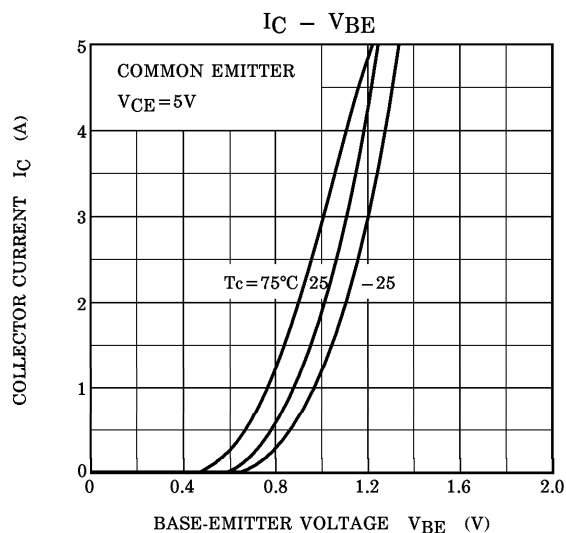
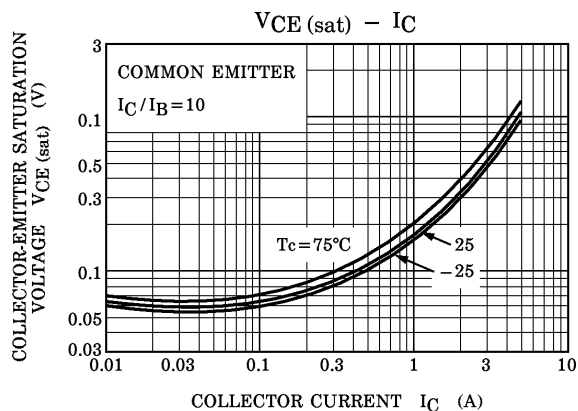
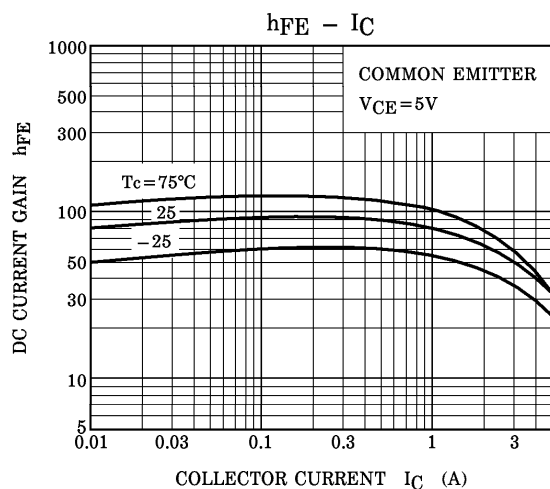
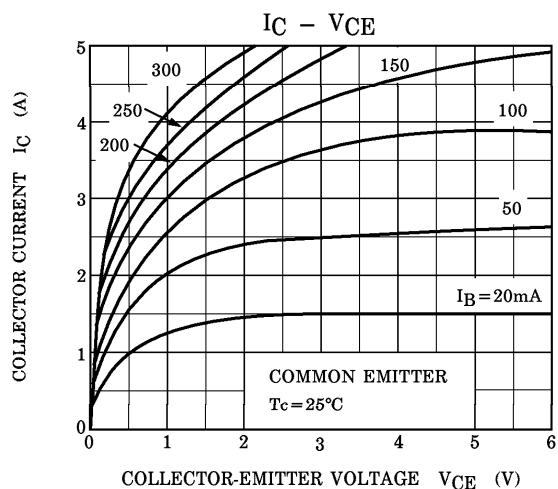
MAXIMUM RATINGS ( $T_c = 25^\circ C$ )

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CBO}$	100	V
Collector-Emitter Voltage	$V_{CEO}$	100	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Collector Current	$I_C$	5	A
Base Current	$I_B$	0.5	A
Collector Power Dissipation ( $T_c = 25^\circ C$ )	$P_C$	40	W
Junction Temperature	$T_j$	150	$^\circ C$
Storage Temperature Range	$T_{stg}$	$-55 \sim 150$	$^\circ C$

ELECTRICAL CHARACTERISTICS ( $T_c = 25^\circ C$ )

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CBO}$	$V_{CB}=100V, I_E=0$	—	—	100	$\mu A$
Emitter Cut-off Current	$I_{EBO}$	$V_{EB}=5V, I_C=0$	—	—	1	mA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=50mA, I_B=0$	100	—	—	V
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE}=5V, I_C=1A$	40	—	240	
	$h_{FE(2)}$	$V_{CE}=5V, I_C=4A$	20	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=4A, I_B=0.4A$	—	—	2.0	V
Base-Emitter Voltage	$V_{BE}$	$V_{CE}=5V, I_C=1A$	—	—	1.5	V
Transition Frequency	$f_T$	$V_{CE}=5V, I_C=1A$	—	12	—	MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB}=10V, I_E=0, f=1MHz$	—	100	—	pF

Note :  $h_{FE(1)}$  Classification    R : 40~80,    O : 70~140,    Y : 120~240



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